Features

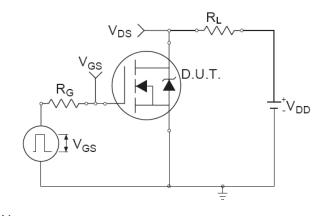
- V_{DSS} =200V/ V_{GSS} =±25V/ I_{D} =9A $R_{DS(ON)}$ =5m Ω (max.)@ V_{GS} =10V
- Low Dense Cell Design
- Reliable and Rugged
- Advanced trench process technology

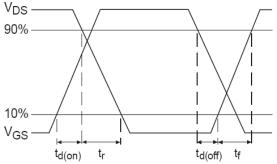
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Applications

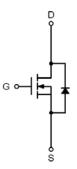
- Synchronous Rectification
- Power Management in Inverter System

Switching Time Test Circuit and Waveforms





Pin Description





Marking and pin Assignment



TO-220-3L top view

Package Marking and Ordering Information

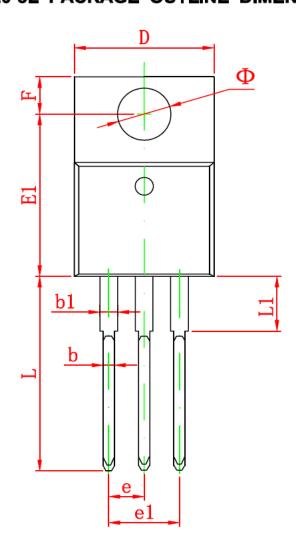
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM741	HM741	TO-220-3L	-	-	-

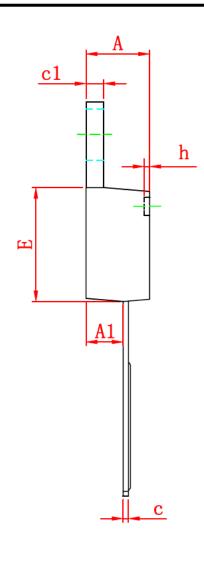
Key Electrical Characteristics (TO-220 package)

Parameter	Description	Min	Typ	Max	Test condition	
BV _{DSS} , V	Drain-to-Source Breakdown Voltage	200	-	-	V _{GS} =0 V, I _D =250 μA	
I _D , A '''''	Continuous Drain "Current	ı	-	9*	Tj = 25 °C	
R _{DS} (on), Ohm	"Static Drain-to-Source On Resistance	ı	0,35	0,4	V _{GS} =10 V, I _D =4,5 A	
V _{GS} (th), V	Gate Threshold Voltage	2,0	-	4,0	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
I _{DSS} , μA	Drain-to-Source Leakage Current	ı	-	1,0	V _{DS} = 200 V, V _{GS} = 0 V	
I _{GSS} , nA	Gate-to-Source Leakage Current	1	-	±100	V_{GS} = ± 25 V, V_{DS} = 0 V	
Tj, T _{STG} , °C	Operating Junction and Storage Temperature Range	- 55 ~ +150				

^{*} Drain current limited by junction temperature

TO-220-3L PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	4.470	4.670	0.176	0.184	
A1	2.520	2.820	0.099	0.111	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
E1	12.060	12.460	0.475	0.491	
е	2.540) TYP	0.100 TYP		
e1	4.980	5.180	0.196	0.204	
F	2.590	2.890	0.102	0.114	
h	0.000	0.300	0.000	0.012	
L	13.400	13.800	0.528	0.543	
L1	3.560	3.960	0.140	0.156	
Ф	3.735	3.935	0.147	0.155	

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